

2SB621, 2SB621A

Silicon PNP epitaxial planer type

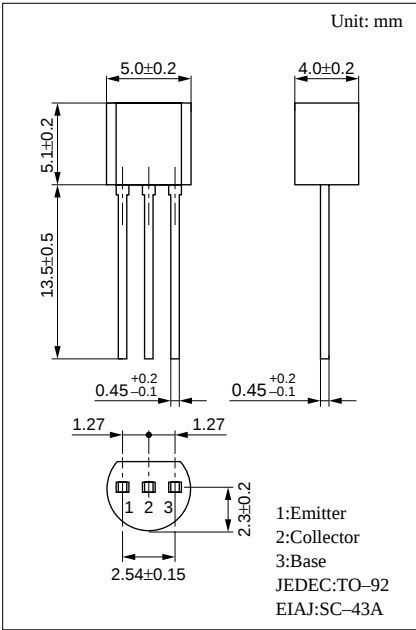
For low-frequency output amplification
Complementary to 2SD592 and 2SD592A

Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$.
- High transition frequency f_T .

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-30	V
2SB621A		-60	
Collector to emitter voltage	V_{CEO}	-25	V
2SB621A		-50	
Emitter to base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-1.5	A
Collector current	I_C	-1	A
Collector power dissipation	P_C	750	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

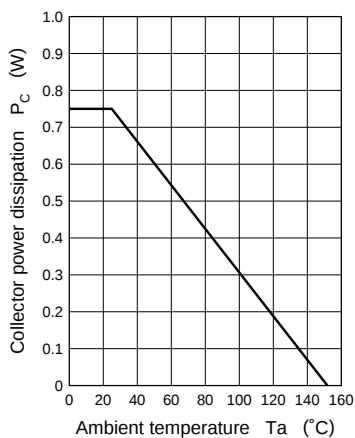
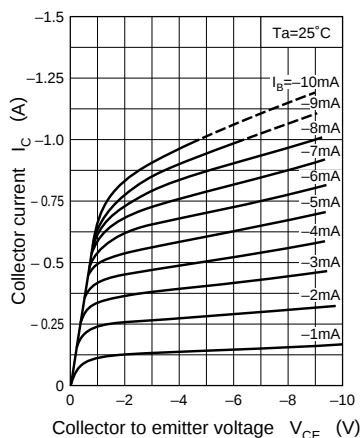
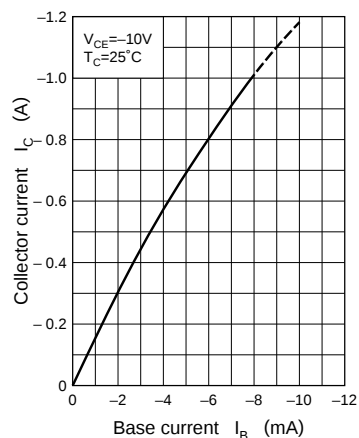
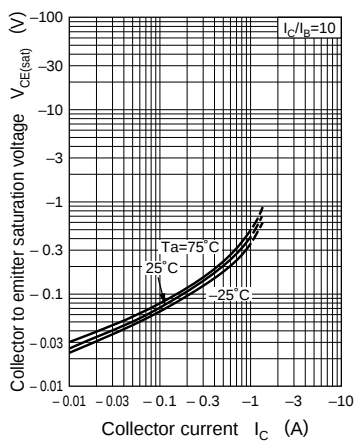
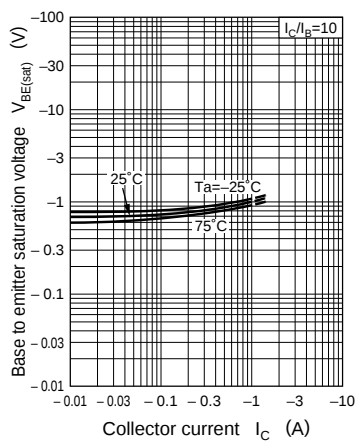
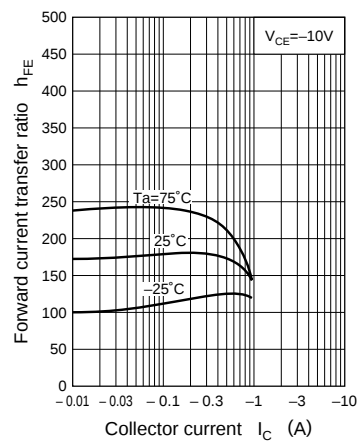
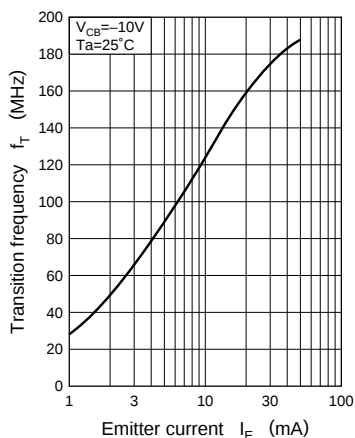
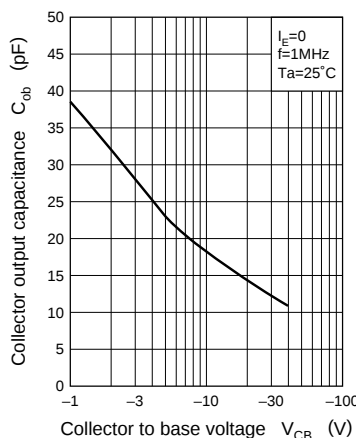


Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -20V, I_E = 0$			-0.1	μA
Collector to base voltage	V_{CBO}	$I_C = -10\mu A, I_E = 0$	-30			V
			-60			
Collector to emitter voltage	V_{CEO}	$I_C = -2mA, I_B = 0$	-25			V
			-50			
Emitter to base voltage	V_{EBO}	$I_E = -10\mu A, I_C = 0$	-5			V
Forward current transfer ratio	h_{FE1}^*	$V_{CE} = -10V, I_C = -500mA$	85		340	
	h_{FE2}	$V_{CE} = -5V, I_C = -1A$	50			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.2	-0.4	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.85	-1.2	V
Transition frequency	f_T	$V_{CB} = -10V, I_E = 50mA, f = 200MHz$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		20	30	pF

* h_{FE1} Rank classification

Rank	Q	R	S
h_{FE1}	85 ~ 170	120 ~ 240	170 ~ 340

$P_C - T_a$  $I_C - V_{CE}$  $I_C - I_B$  $V_{CE(sat)} - I_C$  $V_{BE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $C_{ob} - V_{CB}$  $V_{CER} - R_{BE}$ 